

# Hybrid Memory Cube (HMC)

#### J. Thomas Pawlowski, Fellow

Chief Technologist, Architecture Development Group, Micron jpawlowski@micron.com



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## Outline

- Problems
- Goals
- HMC introduction
- New relationship between CPU and memory
- Internal architecture
- Performance
- Summary

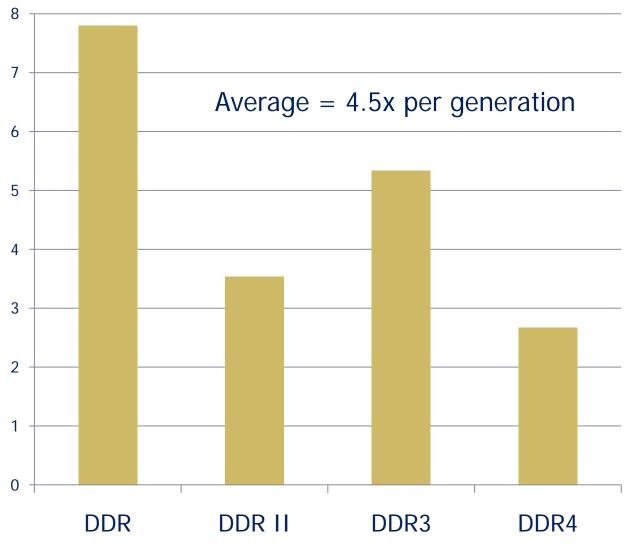


## The Problems

- Observed Problems:
  - Latency (classic "memory wall")
  - Bandwidth related issues
  - Power / energy
  - Many-core, Multi-threaded CPUs generate higher random request rates
  - Memory capacity per unit footprint
- Future Problems:
  - Scalability of bandwidth, densities, request rates and lower latencies
- Essential Underlying Issue: Direct control of memory must give way to memory abstraction
  - Mitigate negative characteristics of next generation DRAM processes
  - Introduction of future DRAM replacement technologies



## Historic Energy x Bandwidth Improvement Per DRAM Generation

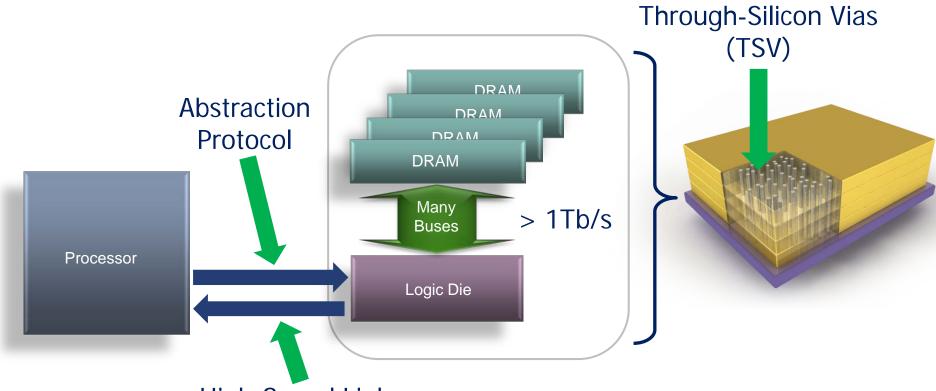




## Hybrid Memory Cube Goals

- 1. Higher bandwidth
- 2. Higher signaling rate
- 3. Lower energy per useful unit of work done
- 4. Lower system latency
- 5. Increased request rate, for many-core: **CONCURRENCY**!
- 6. Higher memory packing density
- 7. Abstracted interface
  - 1. lighten CPU/DRAM interaction
  - 2. enable new DRAM management concepts
  - 3. manage future process scaling and future technology introductions
- 8. Scalability for higher future bandwidths and density footprint
- 9. Reduce customer and Micron time to market

## Hybrid Memory Cube (HMC)



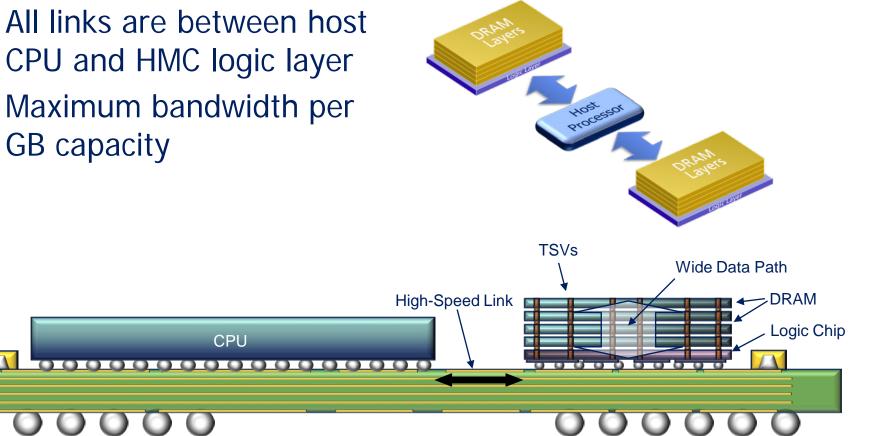
High-Speed Links

Notes: Tb/s = Terabits / second HMC height is exaggerated

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## HMC Near Memory – MCM Configuration

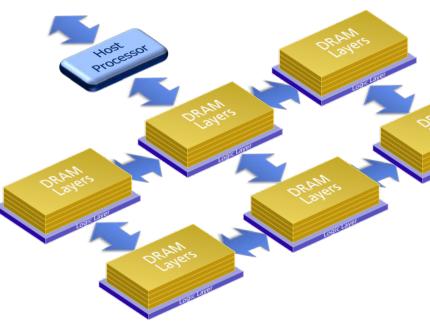
- All links are between host • CPU and HMC logic layer
- Maximum bandwidth per **GB** capacity



Notes: MCM = multi-chip module Illustrative purposes only; height is exaggerated

## HMC "Far" Memory

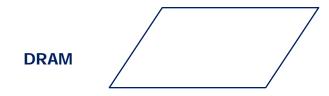
- Far memory
  - Some HMC links connect to host, some to other cubes
  - Serial links form networks of cubes
    - the memory = the network
  - Scalable to meet system requirements
  - Can be in module form or soldereddown
  - Can form a variety of topologies e.g., tree, ring, double-ring, mesh
- Future interfaces
  - Higher speed electrical (SERDES)
  - Optical
  - Whatever the most appropriate interface for the job



## **Processor – Memory Interaction**

- Yesterday: multi-core CPU direct connection to DRAM-specific buses
  - Complex scheduler, deep queues, high reordering especially writes
  - Many DRAM timing parameters standardized across vendors Worst case "everything"
  - Result is conservative, evolutionary, uncreative, slow performance growth
- Now: direct connect to HMC logic chip via abstracted high-speed interface
  - No need for complex scheduler, just thin arbiter, shallow queues
  - Only the high-speed interface, protocol, form-factor might be standardized NO TIMING constraints, overrun is prevented
  - Great innovations can occur "under the hood"
  - Maximize performance growth
  - Logic layer flexibility allows HMC cubes to be designed for multiple platforms and applications without changing the high-volume DRAM
- HMC takes requests, delivers results in most advantageous order

#### Start with a clean slate





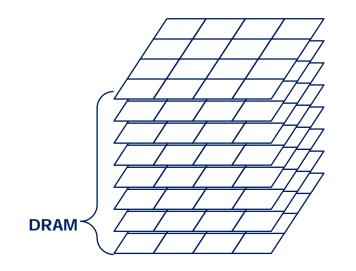
Re-partition the DRAM and strip away the common logic

DRAM





#### Stack multiple DRAMs





#### Re-insert common logic on to the Logic Base die

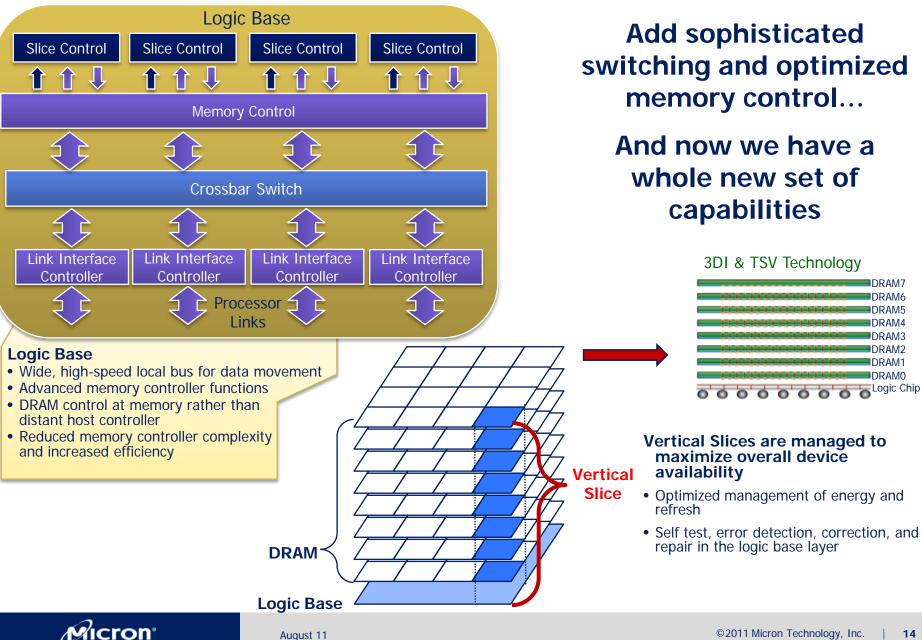
#### DRAM3 DRAM2 **DRAM1 DRAMO** Chip 000000000 Vertical Slices are managed to maximize overall device availability Vertical Slice Optimized management of energy and refresh Self test, error detection, correction, and repair in the logic base layer DRAM Logic Base



3DI & TSV Technology

DRAM7 DRAM6 DRAM5

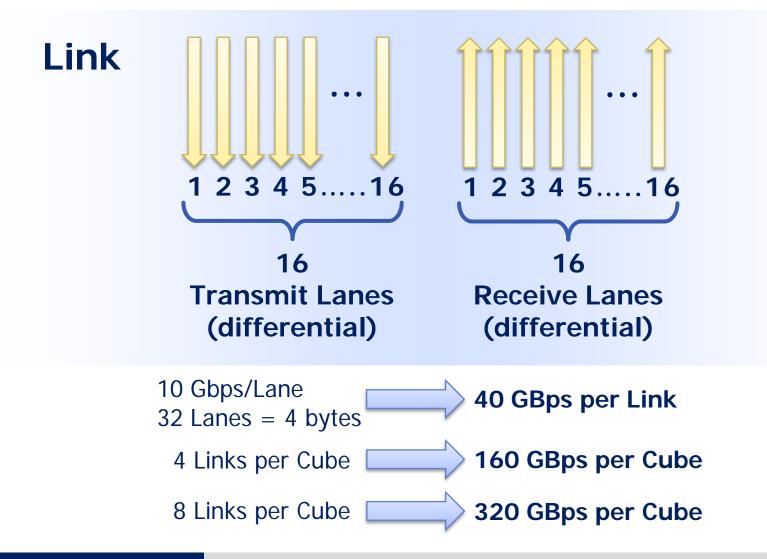
DRAM4



## Vastly More Responders

- Conventional DRAM DIMM example: 8 devices, 8 banks/device
  - Banks of all devices run in lock-step
  - One of 8 potential responders will answer a typical request
- Not only does HMC give excellent concurrency
  - HMC gen 1 example: 4 DRAMs \* 16 slices \* 2 banks = 128
  - One of 128 potential responders will answer a typical request
  - Double that to 256 if 8 DRAMs are in the stack
  - Vast improvement in response to random request stream
- Significant impact on system latency
  - DRAM tRC is lower by design
  - Lower queue delays and higher bank availability further shortens latency
  - Serial links slightly increase latency
  - Net effect is a substantial system latency reduction

#### Available Total Bandwidth



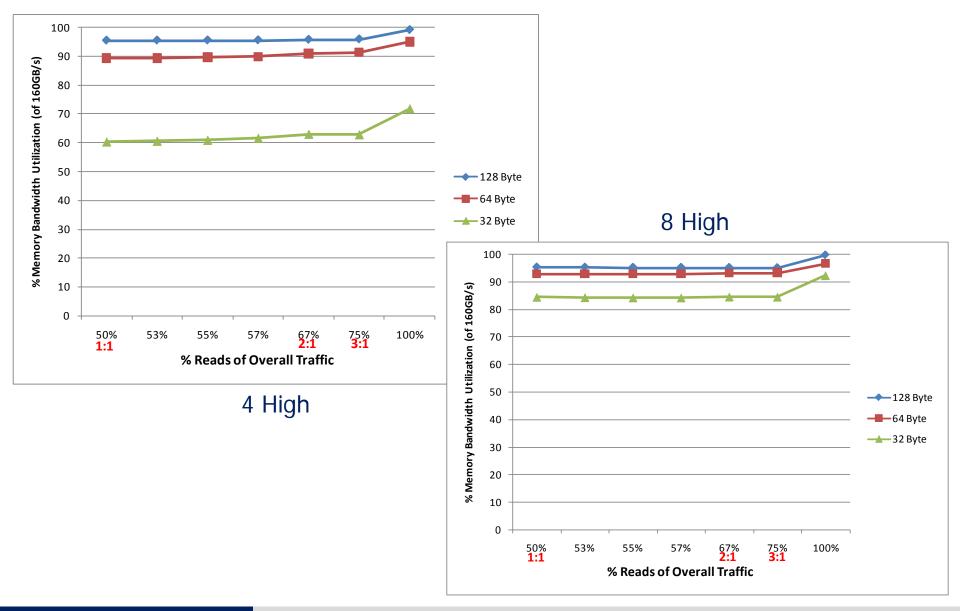
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#### **RAS** Features

- Reliability, Availability, and Serviceability (RAS) features are built into HMC
- Systemic RAS features
  - Array repair
  - DRAM/Logic IO interface repair
- Internal ECC is utilized for detection and short term correction
  - Upon detection, repair is scheduled so that ECC is not a perpetual crutch for an identified issue and is free to cover future errors
- Link IO has means to detect communication errors
  - Worst case hard failure shuts down only one of many links

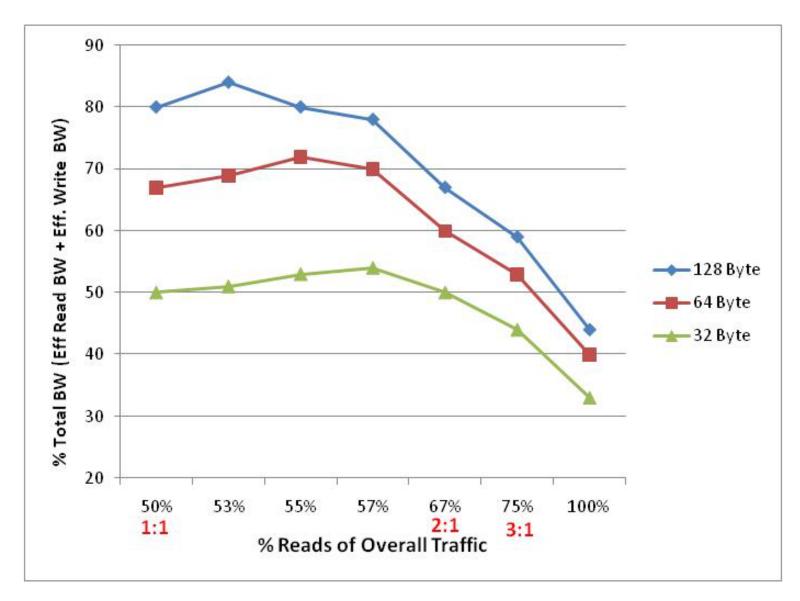


## Internal DRAM Efficiency 4-8 High Stacks



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### Effective Read/Write External Link Efficiency





## **Other Unique System Capabilities**

- Request rate capability
  - 3.2G operations per second (32 byte data transactions)
  - Limited by external data links
    - 2.3Gops at 128GB/s, 2.9Gops at 160GB/s
- Random request capability
  - Historically this gets worse as bandwidth is increased
  - DDR3 SDRAM is ~29% at BL8, DDR4 is worse, GDDR5 is worse yet
  - HMC achieves 75% of peak bandwidth (64B data transactions)
- Network of HMCs
  - E.g., double-ring or mesh of interconnected HMCs
  - Average latency grows but is a constant regardless of the individual HMC's depth in the mesh



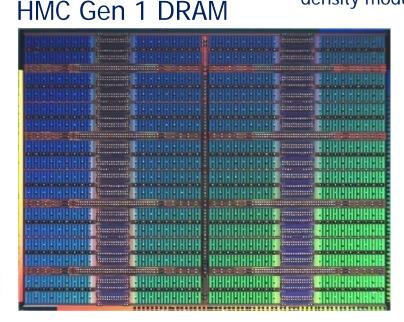
## HMC<sub>Gen1</sub>: Technology Comparison

Generation 1 (4 + 1 memory configuration)

| Technology             | VDD | IDD  | BW GB/s | Power (W) | mW/GB/s | pj∕bit | real pJ/bit |
|------------------------|-----|------|---------|-----------|---------|--------|-------------|
| SDRAM PC133 1GB Module | 3.3 | 1.50 | 1.06    | 4.96      | 4664.97 | 583.12 | 762         |
| DDR-333 1GB Module     | 2.5 | 2.19 | 2.66    | 5.48      | 2057.06 | 257.13 | 245         |
| DDRII-667 2GB Module   | 1.8 | 2.88 | 5.34    | 5.18      | 971.51  | 121.44 | 139         |
| DDR3-1333 2GB Module   | 1.5 | 3.68 | 10.66   | 5.52      | 517.63  | 64.70  | 52          |
| DDR4-2667 4GB Module   | 1.2 | 5.50 | 21.34   | 6.60      | 309.34  | 38.67  | 39          |
| HMC, 4 DRAM w/ Logic   | 1.2 | 9.23 | 128.00  | 11.08     | 86.53   | 10.82  | 13.7        |

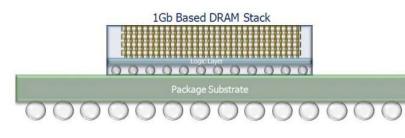
Simple calculation from IDD7 (SDRAM IDD4)

Real system, some with lower density modules

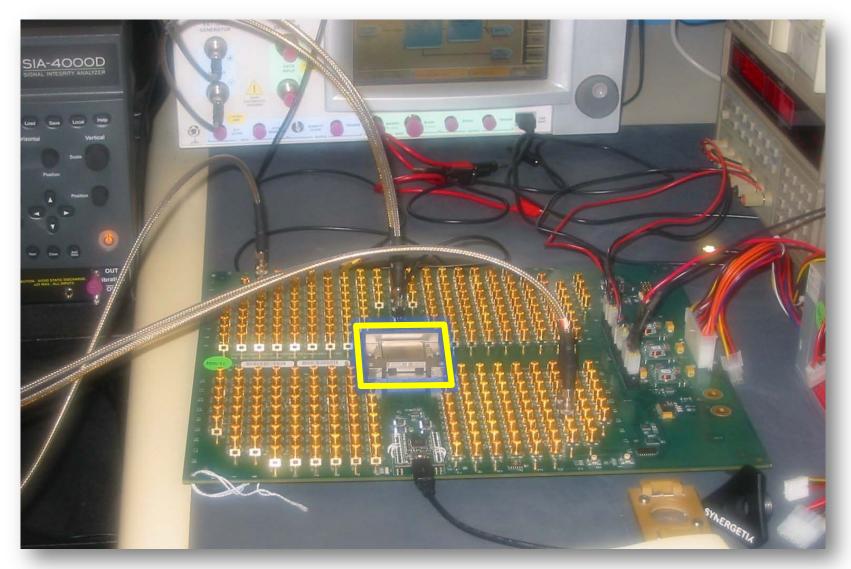


• 1Gb 50nm DRAM Array

- 90nm prototype logic
- 512MB total DRAM cube
- 128GB/s Bandwidth
- 27mm x 27mm prototype
- Functional demonstrations!
- Reduced host CPU energy



#### **HMC** Demonstration Platform





## Summary

- Revolutionary DRAM performance improvement demonstrated by
  - Changing to abstracted high-speed buses
  - Employing 3D packaging using a hybrid of DRAM and logic technologies
  - Pulling in and improving the DRAM controller
  - Marrying DRAM and logic together using many TSVs
  - Completely rethinking DRAM architecture to exploit 3D
  - Managing component health for robust system solutions
- Result is >10x bandwidth, <1/3 energy, lower latency
- Request rates far beyond 2 billion operations per second
- Logic layer flexibility allows HMC to be tailor-made for multiple platforms and applications
- Scalable to ANY performance level. Imagine the possibilities.

## Energy x Bandwidth Improvement Per DRAM Generation



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